

# Miao Xu

## List of Publications by Citations

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108  
papers

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72  
g-index

108  
ext. papers

5,678  
ext. citations

4.6  
avg, IF

5.48  
L-index

#	Paper	IF	Citations
108	Enhanced power-conversion efficiency in polymer solar cells using an inverted device structure. <i>Nature Photonics</i> , <b>2012</b> , 6, 591-595	33.9	3384
107	Manipulation of Charge and Exciton Distribution Based on Blue Aggregation-Induced Emission Fluorophors: A Novel Concept to Achieve High-Performance Hybrid White Organic Light-Emitting Diodes. <i>Advanced Functional Materials</i> , <b>2016</b> , 26, 776-783	15.6	171
106	Manipulation of exciton distribution for high-performance fluorescent/phosphorescent hybrid white organic light-emitting diodes. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 7668-7683	7.1	84
105	High-performance doping-free hybrid white organic light-emitting diodes: The exploitation of ultrathin emitting nanolayers (. <i>Nano Energy</i> , <b>2016</b> , 26, 26-36	17.1	84
104	A flexible AMOLED display on the PEN substrate driven by oxide thin-film transistors using anodized aluminium oxide as dielectric. <i>Journal of Materials Chemistry C</i> , <b>2014</b> , 2, 1255-1259	7.1	69
103	High performance indium-zinc-oxide thin-film transistors fabricated with a back-channel-etch-technique. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 253501	3.4	67
102	High-Performance Doping-Free Hybrid White OLEDs Based on Blue Aggregation-Induced Emission Luminogens. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 34162-34171	9.5	59
101	Enhanced moisture barrier performance for ALD-encapsulated OLEDs by introducing an organic protective layer. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 4017-4024	7.1	51
100	. <i>IEEE Electron Device Letters</i> , <b>2012</b> , 33, 827-829	4.4	50
99	Harnessing charge and exciton distribution towards extremely high performance: the critical role of guests in single-emitting-layer white OLEDs. <i>Materials Horizons</i> , <b>2015</b> , 2, 536-544	14.4	44
98	Extremely stable-color flexible white organic light-emitting diodes with efficiency exceeding 100 lm W <sup>-1</sup> . <i>Journal of Materials Chemistry C</i> , <b>2014</b> , 2, 9836-9841	7.1	44
97	Full-color quantum dots active matrix display fabricated by ink-jet printing. <i>Science China Chemistry</i> , <b>2017</b> , 60, 1349-1355	7.9	41
96	Efficient hybrid white organic light-emitting diodes with extremely long lifetime: the effect of n-type interlayer. <i>Scientific Reports</i> , <b>2014</b> , 4, 7198	4.9	39
95	High Mobility Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistor by Aluminum Oxide Passivation Layer. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 879-882	4.4	38
94	Investigation and optimization of each organic layer: A simple but effective approach towards achieving high-efficiency hybrid white organic light-emitting diodes. <i>Organic Electronics</i> , <b>2014</b> , 15, 926-935	3.5	35
93	Role of Rare Earth Ions in Anodic Gate Dielectrics for Indium-Zinc-Oxide Thin-Film Transistors. <i>Journal of the Electrochemical Society</i> , <b>2012</b> , 159, H502-H506	3.9	35
92	Very-High Color Rendering Index Hybrid White Organic Light-Emitting Diodes with Double Emitting Nanolayers. <i>Nano-Micro Letters</i> , <b>2014</b> , 6, 335-339	19.5	32

91	Regulating charges and excitons in simplified hybrid white organic light-emitting diodes: The key role of concentration in single dopant host-guest systems. <i>Organic Electronics</i> , <b>2014</b> , 15, 2616-2623	3.5	30
90	Influence of source and drain contacts on the properties of the indium-zinc oxide thin-film transistors based on anodic aluminum oxide gate dielectrics. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 103703 <sup>25</sup>	2.5	29
89	Doping-free tandem white organic light-emitting diodes. <i>Science Bulletin</i> , <b>2017</b> , 62, 1193-1200	10.6	28
88	Realization of highly-dense Al <sub>2</sub> O <sub>3</sub> gas barrier for top-emitting organic light-emitting diodes by atomic layer deposition. <i>RSC Advances</i> , <b>2015</b> , 5, 104613-104620	3.7	26
87	Influence of source and drain contacts on the properties of indium-gallium-zinc-oxide thin-film transistors based on amorphous carbon nanofilm as barrier layer. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 3633-40	9.5	25
86	An ideal host-guest system to accomplish high-performance greenish yellow and hybrid white organic light-emitting diodes. <i>Organic Electronics</i> , <b>2015</b> , 27, 29-34	3.5	23
85	Comprehensive Study on the Electron Transport Layer in Blue Fluorescent Organic Light-Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , <b>2013</b> , 2, R258-R261	2	23
84	Direct patterning of silver electrodes with 2.4 $\mu$ m channel length by piezoelectric inkjet printing. <i>Journal of Colloid and Interface Science</i> , <b>2017</b> , 487, 68-72	9.3	22
83	High-performance back-channel-etched thin-film transistors with amorphous Si-incorporated SnO <sub>2</sub> active layer. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 112106	3.4	22
82	Method for Fabricating Amorphous Indium-Zinc-Oxide Thin-Film Transistors With Copper Source and Drain Electrodes. <i>IEEE Electron Device Letters</i> , <b>2015</b> , 36, 342-344	4.4	21
81	Realization of AlO/MgO laminated structure at low temperature for thin film encapsulation in organic light-emitting diodes. <i>Nanotechnology</i> , <b>2016</b> , 27, 494003	3.4	21
80	Simultaneous achievement of low efficiency roll-off and stable color in highly efficient single-emitting-layer phosphorescent white organic light-emitting diodes. <i>Journal of Materials Chemistry C</i> , <b>2014</b> , 2, 5870-5877	7.1	21
79	Highly efficient red phosphorescent organic light-emitting diodes based on solution processed emissive layer. <i>Journal of Luminescence</i> , <b>2013</b> , 142, 35-39	3.8	21
78	Light extraction of flexible OLEDs based on transparent polyimide substrates with 3-D photonic structure. <i>Organic Electronics</i> , <b>2017</b> , 44, 225-231	3.5	20
77	A Low-Power High-Stability Flexible Scan Driver Integrated by IZO TFTs. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 1779-1782	2.9	20
76	Effects of Etching Residue on Positive Shift of Threshold Voltage in Amorphous Indium-Zinc-Oxide Thin-Film Transistors Based on Back-Channel-Etch Structure. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 92-97	2.9	20
75	Performance improvement of oxide thin-film transistors with a two-step-annealing method. <i>Solid-State Electronics</i> , <b>2014</b> , 91, 9-12	1.7	20
74	Damage-free back channel wet-etch process in amorphous indium-zinc-oxide thin-film transistors using a carbon-nanofilm barrier layer. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 11318-25	9.5	20

73	Trap-Assisted Enhanced Bias Illumination Stability of Oxide Thin Film Transistor by Praseodymium Doping. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 5232-5239	9.5	20
72	Efficient single-emitting layer hybrid white organic light-emitting diodes with low efficiency roll-off, stable color and extremely high luminance. <i>Journal of Industrial and Engineering Chemistry</i> , <b>2015</b> , 30, 85-91	6.3	19
71	Effect of ITO Serving as a Barrier Layer for Cu Electrodes on Performance of a-IGZO TFT. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 504-507	4.4	18
70	Fabrication of Flexible Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors by a Chemical Vapor Deposition-Free Process on Polyethylene Naphthalate. <i>ECS Journal of Solid State Science and Technology</i> , <b>2014</b> , 3, Q3035-Q3039	2	18
69	Impact of Deposition Temperature of the Silicon Oxide Passivation on the Performance of Indium Zinc Oxide Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 076501	1.4	18
68	TFT-Directed Electroplating of RGB Luminescent Films without a Vacuum or Mask toward a Full-Color AMOLED Pixel Matrix. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 17519-17525	9.5	18
67	A High-Reliability Gate Driver Integrated in Flexible AMOLED Display by IZO TFTs. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 1991-1996	2.9	17
66	High mobility flexible polymer thin-film transistors with an octadecyl-phosphonic acid treated electrochemically oxidized alumina gate insulator. <i>Journal of Materials Chemistry C</i> , <b>2015</b> , 3, 7062-7066	7.1	17
65	High-performance hybrid white organic light-emitting diodes employing p-type interlayers. <i>Journal of Industrial and Engineering Chemistry</i> , <b>2015</b> , 27, 240-244	6.3	17
64	High-Performance Hybrid White Organic Light-Emitting Diodes Comprising Ultrathin Blue and Orange Emissive Layers. <i>Applied Physics Express</i> , <b>2013</b> , 6, 122101	2.4	17
63	Gate bias stress stability under light irradiation for indium zinc oxide thin-film transistors based on anodic aluminium oxide gate dielectrics. <i>Journal Physics D: Applied Physics</i> , <b>2011</b> , 44, 455102	3	17
62	Effect of Post Treatment For Cu-Cr Source/Drain Electrodes on a-IGZO TFTs. <i>Materials</i> , <b>2016</b> , 9,	3.5	17
61	Effect of Al <sub>2</sub> O <sub>3</sub> Passivation Layer and Cu Electrodes on High Mobility of Amorphous IZO TFT. <i>IEEE Journal of the Electron Devices Society</i> , <b>2018</b> , 6, 733-737	2.3	16
60	Mobility Enhancement in Amorphous In-Ga-Zn-O Thin-Film Transistor by Induced Metallic in Nanoparticles and Cu Electrodes. <i>Nanomaterials</i> , <b>2018</b> , 8,	5.4	16
59	A Highly Stable Biside Gate Driver Integrated by IZO TFTs. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 3335-3338	2.9	16
58	Flexible organic field-effect transistors with high-reliability gate insulators prepared by a room-temperature, electrochemical-oxidation process. <i>RSC Advances</i> , <b>2015</b> , 5, 15695-15699	3.7	15
57	High-mobility ZrInO thin-film transistor prepared by an all-DC-sputtering method at room temperature. <i>Scientific Reports</i> , <b>2016</b> , 6, 25000	4.9	15
56	Investigation on spacers and structures: A simple but effective approach toward high-performance hybrid white organic light emitting diodes. <i>Synthetic Metals</i> , <b>2013</b> , 184, 5-9	3.6	15

55	Analytical Extraction Method for Density of States in Metal Oxide Thin-Film Transistors by Using Low-Frequency Capacitance-Voltage Characteristics. <i>Journal of Display Technology</i> , <b>2016</b> , 12, 888-891		15
54	Power Consumption Model for AMOLED Display Panel Based on 2T-1C Pixel Circuit. <i>Journal of Display Technology</i> , <b>2016</b> , 12, 1064-1069		15
53	Improvement of Mobility and Stability in Oxide Thin-Film Transistors Using Triple-Stacked Structure. <i>IEEE Electron Device Letters</i> , <b>2016</b> , 37, 57-59	4.4	14
52	. <i>Journal of Display Technology</i> , <b>2013</b> , 9, 572-576		14
51	A Low-Power Ring Oscillator Using Pull-Up Control Scheme Integrated by Metal Oxide TFTs. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 4946-4951	2.9	14
50	A novel nondestructive testing method for amorphous Si <sub>3</sub> N <sub>4</sub> films. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 505102	3	14
49	Improving Thermal Stability of Solution-Processed Indium Zinc Oxide Thin-Film Transistors by Praseodymium Oxide Doping. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 28764-28771	9.5	13
48	The effect of spacer in hybrid white organic light emitting diodes. <i>Science Bulletin</i> , <b>2014</b> , 59, 3090-3097		13
47	Simplified hybrid white organic light-emitting diodes with efficiency/efficiency roll-off/color rendering index/color-stability trade-off. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2014</b> , 8, 719-723	2.5	13
46	Effects of praseodymium doping on the electrical properties and aging effect of InZnO thin-film transistor. <i>Journal of Materials Science</i> , <b>2019</b> , 54, 14778-14786	4.3	12
45	High-Resolution Flexible AMOLED Display Integrating Gate Driver by Metal Oxide TFTs. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 1660-1663	4.4	12
44	All-Aluminum Thin Film Transistor Fabrication at Room Temperature. <i>Materials</i> , <b>2017</b> , 10,	3.5	11
43	High-mobility flexible thin-film transistors with a low-temperature zirconium-doped indium oxide channel layer. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2016</b> , 10, 493-497	2.5	11
42	Low-Power Bi-Side Scan Driver Integrated by IZO TFTs Including a Clock-Controlled Inverter. <i>Journal of Display Technology</i> , <b>2014</b> , 10, 523-525		10
41	Effect of Intrinsic Stress on Structural and Optical Properties of Amorphous Si-Doped SnO <sub>2</sub> Thin-Film. <i>Materials</i> , <b>2017</b> , 10,	3.5	10
40	A room temperature strategy towards enhanced performance and bias stability of oxide thin film transistor with a sandwich structure channel layer. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 153503	3.4	9
39	Reduced contact resistance of a-IGZO thin film transistors with inkjet-printed silver electrodes. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 165103	3	9
38	Highly stable amorphous indium-zinc-oxide thin-film transistors with back-channel wet-etch process. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2014</b> , 8, 176-181	2.5	9

37	High reliability amorphous oxide semiconductor thin-film transistors gated by buried thick aluminum. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2012</b> , 6, 403-405	2.5	9
36	Low-temperature, high-stability, flexible thin-film transistors with a novel $\text{ScxIn1-xO3}$ semiconductor. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 24LT01	3	9
35	The effect of charge transfer transition on the photostability of lanthanide-doped indium oxide thin-film transistors. <i>Communications Materials</i> , <b>2021</b> , 2,	6	8
34	High-Performance and Flexible Neodymium- Doped Oxide Semiconductor Thin-Film Transistors With Copper Alloy Bottom-Gate Electrode. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 839-842	4.4	7
33	Island-Like AZO/ $\text{Al}_2\text{O}_3$ Bilayer Channel Structure for Thin Film Transistors. <i>Advanced Materials Interfaces</i> , <b>2017</b> , 4, 1700063	4.6	6
32	Facilitation of transparent gas barrier using $\text{SiN}_x/\text{a-IZO}$ lamination for organic light emitting diodes. <i>Organic Electronics</i> , <b>2015</b> , 24, 57-64	3.5	6
31	24-4: Flexible AMOLED based on Oxide TFT with High Mobility. <i>Digest of Technical Papers SID International Symposium</i> , <b>2017</b> , 48, 342-344	0.5	5
30	Impact of Deposition Temperature of the Silicon Oxide Passivation on the Performance of Indium Zinc Oxide Thin-Film Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 076501	1.4	5
29	A physics-based model of threshold voltage for amorphous oxide semiconductor thin-film transistors. <i>AIP Advances</i> , <b>2016</b> , 6, 035025	1.5	5
28	Design of high speed gate driver employing IZO TFTs. <i>Displays</i> , <b>2015</b> , 39, 93-99	3.4	4
27	Indium-Gallium-Zinc-Oxide Thin-Film Transistors Based on Homojunctioned Structure Fabricated With a Self-Aligned Process. <i>Journal of Display Technology</i> , <b>2015</b> , 11, 589-595		4
26	A low-power gate driver integrated by IZO-TFTs employing single negative power source. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 065006	1.8	4
25	High-Performance Back-Channel-Etch Thin-Film Transistors With Zinc Tin Oxide as Barrier Layer via Spray Coating. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 3854-3860	2.9	4
24	Dual Gate Indium-Zinc Oxide Thin-Film Transistors Based on Anodic Aluminum Oxide Gate Dielectrics. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 2448-2453	2.9	4
23	Highly transparent and thermal-stable silver nanowire conductive film covered with $\text{ZnMgO}$ by atomic-layer-deposition. <i>Journal of Physics and Chemistry of Solids</i> , <b>2017</b> , 111, 328-334	3.9	4
22	Letter: A new compensation pixel circuit with metal oxide thin-film transistors for active-matrix organic light-emitting diode displays. <i>Journal of the Society for Information Display</i> , <b>2015</b> , 23, 233-239	2.1	3
21	20.4L: Late-News Paper: A Flexible AMOLED Display on PEN Substrate Driven by Oxide Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , <b>2014</b> , 45, 260-262	0.5	3
20	16.2: A 4.8-inch AMOLED Display Panel Driven by Stable Amorphous In-Zn-O Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , <b>2013</b> , 44, 170-173	0.5	3



19	Letter: Solution-processed flexible zinc-tin oxide thin-film transistors on ultra-thin polyimide substrates. <i>Journal of the Society for Information Display</i> , <b>2016</b> , 24, 211-215	2.1	3
18	A low-power D flip flop integrated by metal oxide thin film transistors employing internal feedback control. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 115004	1.8	3
17	A physics-based model of flat-band capacitance for metal oxide thin-film transistors. <i>AIP Advances</i> , <b>2018</b> , 8, 065319	1.5	3
16	Highly conductive AZO thin films obtained by rationally optimizing substrate temperature and oxygen partial pressure. <i>Molecular Crystals and Liquid Crystals</i> , <b>2017</b> , 644, 190-196	0.5	2
15	High-speed low-power voltage-programmed driving scheme for AMOLED displays. <i>Journal of Semiconductors</i> , <b>2015</b> , 36, 125005	2.3	2
14	IZO Protected Silver Films Used as Anodes in Top-Emitting Organic LEDs. <i>ECS Journal of Solid State Science and Technology</i> , <b>2013</b> , 2, R190-R195	2	2
13	Low-Roughness and Easily-Etched Transparent Conducting Oxides with a Stack Structure of ITO and IZO. <i>ECS Journal of Solid State Science and Technology</i> , <b>2013</b> , 2, R245-R248	2	2
12	A metal oxide TFT gate driver with a single negative power source employing a boosting module. <i>Journal of Information Display</i> , <b>2020</b> , 21, 57-64	4.1	2
11	Enhanced Negative-Bias Illumination Temperature Stability of Praseodymium-Doped InGaO Thin-Film Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2021</b> , 218, 2000812	1.6	2
10	Manchester-encoded data transmission circuit integrated by metal oxide TFTs suitable for 13.56 MHz radio-frequency identification tag application. <i>IET Circuits, Devices and Systems</i> , <b>2018</b> , 12, 771-776	1.1	2
9	A Semi-Analytical Extraction Method for Interface and Bulk Density of States in Metal Oxide Thin-Film Transistors. <i>Materials</i> , <b>2018</b> , 11,	3.5	1
8	Flexible amorphous oxide thin-film transistors on polyimide substrate for AMOLED <b>2014</b> ,		1
7	Influence of passivation deposition on the performance of In-Zn-O thin-film transistors based on etch-stopper structure. <i>Materials Research Express</i> , <b>2014</b> , 1, 036402	1.7	1
6	A scan driver including light emission control integrated by metal-oxide thin-film transistors. <i>Semiconductor Science and Technology</i> , <b>2020</b> , 36, 025006	1.8	1
5	Optimization of carrier transport layer: A simple but effective approach toward achieving high efficiency all-solution processed InP quantum dot light emitting diodes. <i>Organic Electronics</i> , <b>2021</b> , 96, 106256	3.5	1
4	High performance and illumination stable In <sub>2</sub> O <sub>3</sub> nanofibers-based field effect transistors by doping praseodymium. <i>Surfaces and Interfaces</i> , <b>2022</b> , 29, 101781	4.1	0
3	A 256 × 256, 50- $\mu$ m Pixel Pitch OPD Image Sensor Based on an IZO TFT Backplane. <i>IEEE Sensors Journal</i> , <b>2021</b> , 21, 20824-20832	4	0
2	An Analytical Frequency-Dependent Capacitance-Voltage Model for Metal Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 1-6	2.9	

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15.2: Invited Paper: Back-Channel-Etch Thin Film Transistors with Zinc Tin Oxide as Barrier Layer via Spray Coating. *Digest of Technical Papers SID International Symposium*, **2019**, 50, 152-152

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